

ISSN 1726-5479

# SENSORS & TRANSDUCERS

9<sup>vol. 96</sup>  
/08

IEEE 1451

 IEEE

TEDS Sensors,  
IEEE 1451 Standards



International Frequency Sensor Association Publishing

 IFSA



# Sensors & Transducers

Volume 96  
Issue 9  
September 2008

[www.sensorsportal.com](http://www.sensorsportal.com)

ISSN 1726-5479

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[www.sensorsportal.com](http://www.sensorsportal.com)

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## Morphological and Humidity Sensing Studies of WO<sub>3</sub> Mixed with ZnO and TiO<sub>2</sub> Powders

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*Received: 17 August 2008 / Accepted: 19 September 2008 / Published: 30 September 2008*

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**Abstract:** This paper reports resistive type humidity sensing properties of composite powder of WO<sub>3</sub>, ZnO and TiO<sub>2</sub> taken in the ratio of 8:2:1. Tungsten oxide powder has been obtained by oxidizing Tungsten powder (Lobachemie, 99 % pure) at 600 °C. 250 mg of ZnO (qualigens, 99% pure) and 125 mg of TiO<sub>2</sub> (qualigens, 98% pure) have been mixed with 1 gram of WO<sub>3</sub>. Pellet of this powder mixture has been made at pressure of 3 tones for half an hour. The pellet has been annealed at temperatures of 300 °C, 400 °C and 500 °C. Humidity sensing application of pellet has been studied in a specially designed chamber. Standard solution of potassium sulphate has been used as humidifier and potassium hydroxide as de-humidifier. Variation in resistances has been noted using Sinometre (MΩ range, VC 9808). Relative humidity is measured using standard hygrometer (Huger, Germany). It has been observed that as relative humidity increases, there is decrease in the resistance of the pellet. After annealing of sample at each temperature, it has been exposed to humidity in the chamber. The mean sensitivity of the pellet is calculated for each annealing temperature. It has been observed that as annealing temperature increases from 300 °C to 500 °C, mean sensitivity increases. This composite material carries a good scope for the development of resistive type humidity sensor. Copyright © 2008 IFSA.

**Keywords:** WO<sub>3</sub>, ZnO, Hygrometer, Sinometre, Annealing, TiO<sub>2</sub>

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### 1. Introduction

Various materials have been studied and used as sensing elements in humidity measurement applications [1-3]. Some metal oxides such as TiO<sub>2</sub>, SnO<sub>2</sub>, ZnO, Cr<sub>2</sub>O<sub>3</sub> and WO<sub>3</sub> are semi-conducting

materials among which  $\text{WO}_3$  has been studied extensively because of its electro-chromic applications. Tungsten oxide and binary systems of tungsten oxide with other metal oxides are also being studied for their gas and humidity sensing applications. Sensors of great variety of application have been developed, numerous materials have been utilized for humidity sensing of which the metal oxides that are physically and chemically stable, have been extensively used at both room and elevated temperature[4-9]. In general, metal oxides have good chemical and thermal stability. Sensors based on change in resistance and capacitance are preferred. In this paper we report the resistive type humidity sensing studies of  $\text{WO}_3$  mixed with ZnO and  $\text{TiO}_2$  Powder.

Specific Sensitivity of the sensor is uniquely defined as the change in resistance ( $\Delta R$ ) of sensing element per unit change in relative humidity (RH %) per unit resistance, i.e.

$$\Delta S = \Delta R / R(\Delta \text{RH} \%) \quad (1)$$

## 2. Experimental Procedure

The starting material is Tungsten powder. When tungsten powder is annealed at temperature  $600^\circ\text{C}$  for three hours it gets converted into tungsten trioxide. Our sample has been prepared by pressing powder  $\text{WO}_3$ , ZnO and  $\text{TiO}_2$  taken in the weight percent ratio 8:2:1, under a load of 3 tones up to half an hour. The pellet so formed has been annealed in an electric furnace at temperature  $300^\circ\text{C}$ ,  $400^\circ\text{C}$  and  $500^\circ\text{C}$  for three hours and after each time of annealing it has been exposed to humidity in the specially designed experimental setup [10-11]. Relative humidity chamber consists of sample holder capable of holding the sample in the form of pellet. The sample pellet has been fitted in this holder and kept in the chamber. The holder carries two copper probes as well connected to a Sino metre used for electrical resistance measurement. Resistance of the sample pellet has been measured after each time of annealing during controlled exposure to humidity in the range of 5 % to 85 %.

## 3. Results and Discussion

The decrease in resistance or increase in conductivity with increasing humidity can be attributed to the mobility of tungsten oxide ions which are loosely attached to the Vander Walls forces of attraction. Adsorption of water makes the material more p-type in nature i.e. the whole concentration is increased by donation of the lone pair from the conducting complex towards the  $\text{WO}_3$  water molecules [12]. Thus the partial charge transfer process of conducting species with that of water molecules results in decrease in resistivity.

Variations of resistance with change in relative humidity are shown in Fig.1, 2 and 3. Fig.1 shows the result of sensing element annealed at  $300^\circ\text{C}$ . This result shows that as humidity increases from 5 to 20 RH%, resistance of sensing element decreases by 37%. The average specific sensitivity in this range is 0.016.

Fig.2 shows the result of the same sensing element annealed at  $400^\circ\text{C}$ . This graph shows that as humidity increases from 5 to 20 RH%, resistance of sensing element decreases by 40%. The average specific sensitivity in this range is 0.016.

Fig.3 shows results for the same sensing element annealed at  $500^\circ\text{C}$ . This result shows that as humidity increases from 5 to 20 RH%, resistance of sensing element decreases by 80%. The average specific sensitivity is 0.031.

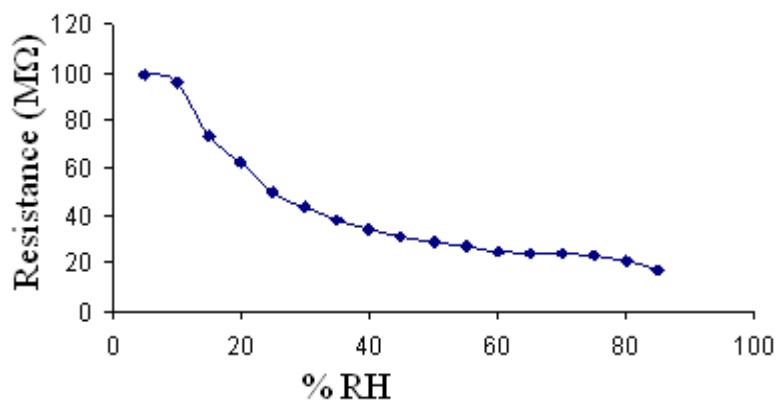


Fig. 1. Variation of Resistance with Change in %RH for sensing element annealed at 300<sup>0</sup>C.

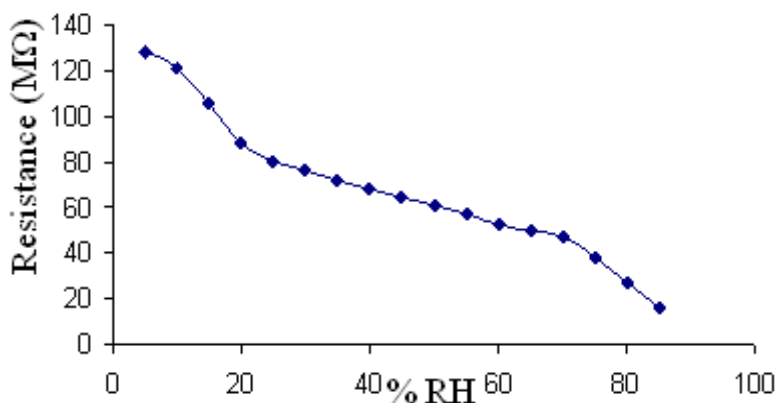


Fig. 2 Variation of Resistance with Change in %RH for sensing element annealed at 400<sup>0</sup>C.

Fig. 2. Variation of Resistance with Change in %RH for sensing element annealed at 400<sup>0</sup>C.

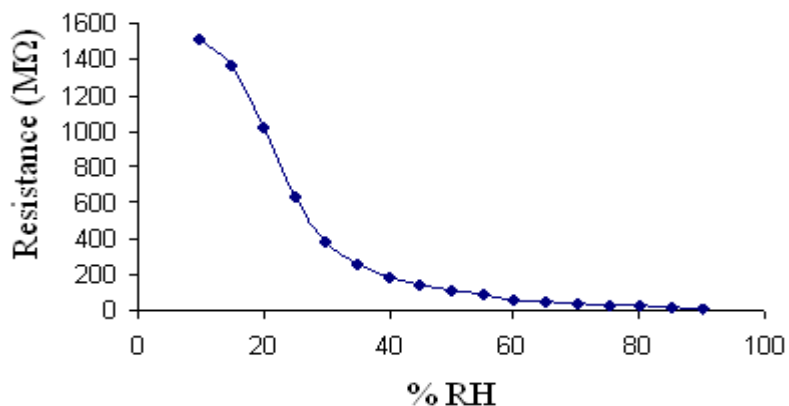


Fig. 3. Variation of Resistance with Change in %RH for sensing element annealed at 500<sup>0</sup>C.

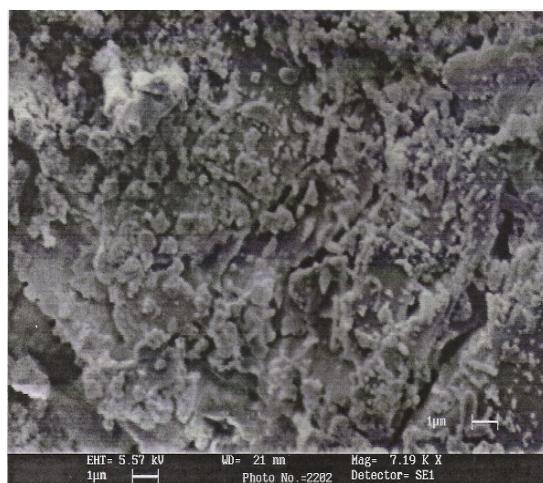
Thus increase in annealing temperature results in increase in sensitivity.

These observations are shown in Table 1.

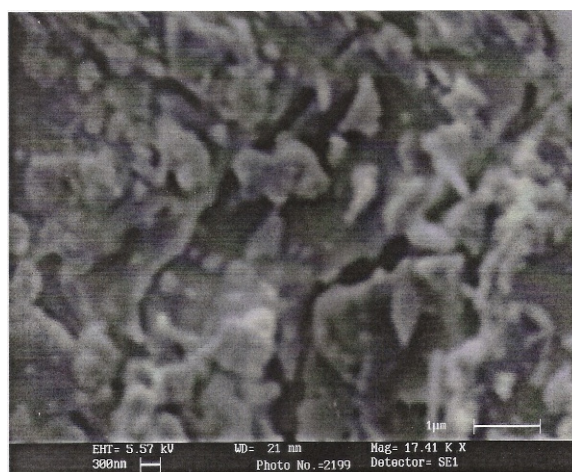
**Table 1.** Annealing temperature vs. relative humidity and sensitivity

Temperature (°C)	RH (%)	Specific Sensitivity	Mean Sensitivity
300	5 to 20	0.020	0.016
	20 to 40	0.022	
	40 to 80	0.010	
400	5 to 20	0.021	0.016
	20 to 40	0.011	
	40 to 80	0.015	
500	10 to 25	0.039	0.031
	25 to 60	0.026	
	60 to 80	0.030	

SEM image of the sample given in Figs.4 and 5 are on micro scale. Fig.4 is the SEM image at low magnification (7.19 Kx) whereas Fig.5 is at high magnification (17.41Kx). SEM images reveal that WO<sub>3</sub> composites nanoparticles combine with adhesive glass particles to form mud particles like clusters leaving spaces as pores.



**Fig. 4.** The SEM image at low magnification (7.19 Kx).



**Fig. 5.** The SEM image at high magnification (17.41Kx).



## Acknowledgement

We are highly obliged to the Geological Survey of India for providing the SEM facility.

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